

um of Plasma Enhanced CVD (PECVD) oxide over which a layer within the range of approximately 0.5 to 2.0 um PECVD nitride is deposited.

14. The method of claim 1 wherein said insulating, separating layer is a polymer dielectric layer or any other appropriate insulating material.

15. The method of claim 1 wherein said insulating, separating layer comprises polyimide.

16. The method of claim 1 wherein said insulating, separating layer comprises the polymer benzocyclobutene (BCB).

17. The method of claim 1 wherein said insulating, separating layer is of a thickness after curing within the range of approximately 1.0 to 30 um.

18. The method of claim 1 wherein said insulating, separating layer is spin-on coated and cured.

19. The method of claim 1 wherein said insulating, separating layer after said spin-on coating is cured at a temperature within the range of approximately 250 to 450 degrees C. for a time

20. The method of claim 16 wherein said insulating, separating layer is subjected to multiple processing steps of spin on coating and curing.

22. The method of claim 1 wherein said openings have an aspect ratio within the range of approximately 1 to 10.

24. The method of claim 1 wherein said metal contacts comprise damascene metal filling.

28. The method of claim 27 wherein said signal pads are mounted in the periphery of said top metalization system and said power and ground connection pads are mounted within the area enclosed